

P-Channel Enhancement Mode MOSFET

Description

The IRLML5203TRPBF uses advanced trench technology

to provide excellent R_{DS(ON)}, This device is suitable

for use as a load switch or in PWM applications.

General Features

 $V_{DS} = -30V, I_{D} = -4.2A$

 $R_{DS(ON)} < 55 m\Omega$ @ V_{GS} =-10V

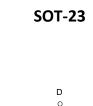
 $R_{DS(ON)}$ < 75m Ω @ V_{GS} =-4.5V

Application

Battery protection

Load switch

Uninterruptible power supply





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLML5203TRPBF	SOT-23	A19T	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	-30	V	
V _G S	Gate-Source Voltage	±12	V	
I _D	Drain Current-Continuous	-4.2	А	
Ірм	Drain Current-Pulsed (Note 1)	-30	А	
P _D	Maximum Power Dissipation	1.2	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	104	°C/W	

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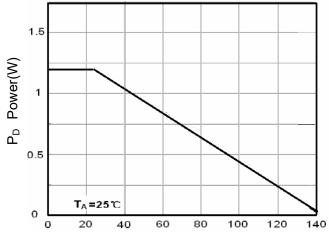
Electrical Characteristics (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-30		-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =-250μA	-0.7	-1	-1.3	V
		V _{GS} =-10V, I _D =-4.2A	-	45	55	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =-4.5V, I _D =-4A	-	56	75	mΩ
		V _{GS} =-2.5V, I _D =-1A		72	90	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4.2A	-	10	-	S
Input Capacitance	C _{lss}		-	880	-	PF
Output Capacitance	Coss	V _{DS} =-15V,V _{GS} =0V,	-	105	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	65	-	PF
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V,I _D =-4.2A V _{GS} =-	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	10V,R _{GEN} =6Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg		-	8.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,I _D =-4.2A,V _{GS} =-	-	1.8	-	nC
Gate-Drain Charge	Q _{gd}	4.5V	-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =-4.2A	_	-	-1.2	V

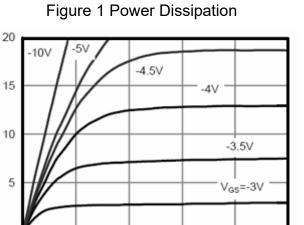
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2、Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3、Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics



T_J-Junction Temperature(℃) Figure 1 Power Dissipation



I_D- Drain Current (A)

0.00

1.00

Vds Drain-Source Voltage (V) Figure 3 Output Characteristics

2.00

3.00

4.00

5.00

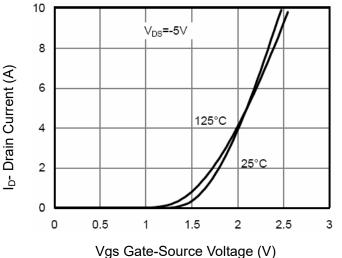
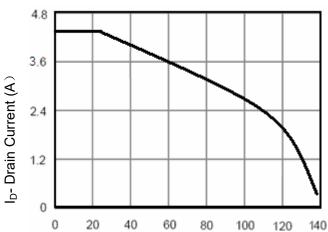
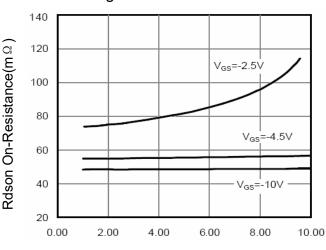


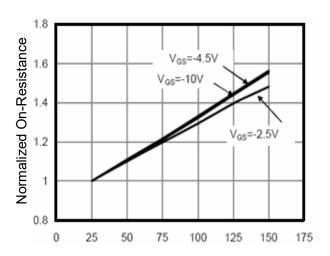
Figure 5 Transfer Characteristics



T_J-Junction Temperature(°C) Figure 2 Drain Current



I_D- Drain Current (A) Figure 4 Drain-Source On-Resistance



 $\label{eq:TJ-Junction} T_{J}\mbox{-Junction Temperature}({}^{\circ}\!\mathbb{C})$ Figure 6 Drain-Source On-Resistance

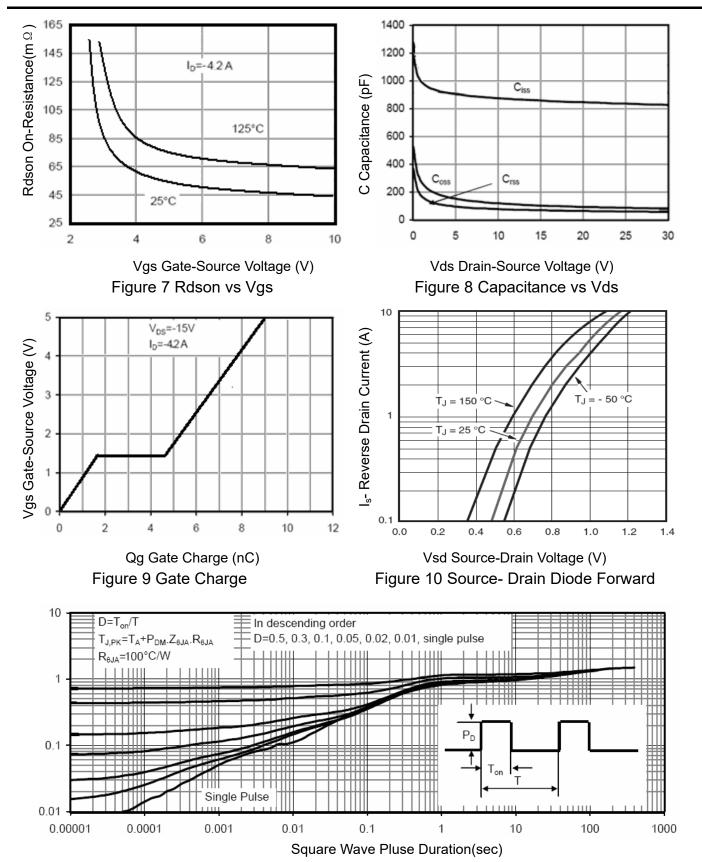
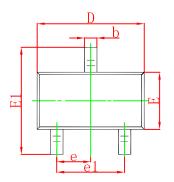
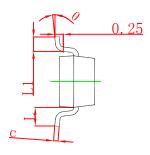


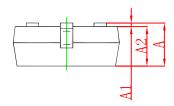
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

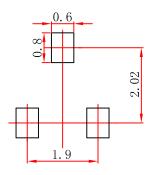






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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